



**AO3410**

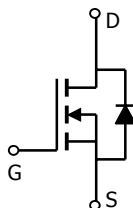
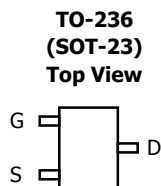
**N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO3410 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V and as high as 12V. This device is suitable for use as a load switch or in PWM applications.

**Features**

- $V_{DS}$  (V) = 30V
- $I_D$  = 5.8 A
- $R_{DS(ON)} < 28m\Omega$  ( $V_{GS} = 10V$ )
- $R_{DS(ON)} < 33m\Omega$  ( $V_{GS} = 4.5V$ )
- $R_{DS(ON)} < 52m\Omega$  ( $V_{GS} = 2.5V$ )
- $R_{DS(ON)} < 70m\Omega$  ( $V_{GS} = 1.8V$ )



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ\text{C}$	5.8	A
	$T_A=70^\circ\text{C}$	4.9	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$T_A=25^\circ\text{C}$	1.4	W
	$T_A=70^\circ\text{C}$	1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	65	90	$^\circ\text{C/W}$
		85	125	
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	43	60	$^\circ\text{C/W}$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.5	0.8	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=5.8\text{A}$ $T_J=125^\circ\text{C}$		23 29	28 39	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=5\text{A}$		26	33	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=4\text{A}$		35	42	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$ , $I_D=3\text{A}$		54	72	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=5\text{A}$	12	17		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.66	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		767		pF
$C_{oss}$	Output Capacitance			111		pF
$C_{rss}$	Reverse Transfer Capacitance			82		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.3		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=5.8\text{A}$		10		nC
$Q_{gs}$	Gate Source Charge			1.2		nC
$Q_{gd}$	Gate Drain Charge			3.1		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=2.7\Omega$ , $R_{GEN}=6\Omega$		5		ns
$t_r$	Turn-On Rise Time			5.5		ns
$t_{D(off)}$	Turn-Off DelayTime			39		ns
$t_f$	Turn-Off Fall Time			4.7		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		15		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		7.1		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.